Vishay Semiconductors

Hyperfast Rectifier, 3 A FRED Pt[®]



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SMC (DO-214AB)

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I _{F(AV)}	3 A				
V _R	100 V				
V _F at I _F	0.69 V				
t _{rr}	25 ns				
T _J max.	175 °C				
Package	SMC (DO-214AB)				
Circuit configuration	Single				

FEATURES

- Hyperfast recovery time, reduced Q_{rr}, and soft recovery
- °C maximum 175 operating junction temperature
- · Specified for output and snubber operation
- · Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

MECHANICAL DATA

Case: SMC (DO-214AB)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	V _{RRM}		100	V		
Average rectified forward current	I _{F(AV)}	T _{Sp} = 142 °C	3	Δ		
Non-repetitive peak surge current	I _{FSM}	$T_J = 25 \ ^{\circ}C$, 6 ms square pulse	130	A		
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C		

ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	100	-	-		
Forward voltage, per diode	V _F	I _F = 3 A	-	0.83	0.90	V	
		I _F = 3 A, T _J = 125 °C	-	0.69	0.75		
Reverse leakage current, per diode	I_	V _R = V _R rated	-	-	2	μA	
neverse leakage current, per diode	I _R	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	1	10	μΑ	
Junction capacitance	CT	V _R = 100 V	-	23	-	pF	

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RoHS

COMPLIANT HALOGEN

FREE



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50$	A/ μ s, V _R = 30 V	-	27	-		
Boyoroo rocoyory timo	+	I _F = 0.5 A, I _R = 1 A,	I _{rr} = 0.25 A	-	-	25	ns	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	18	-		
		T _J = 125 °C	I _F = 3 A, dI _F /dt = 200 A/µs, V _B = 100 V	-	30	-		
Poole recovery ourrent		T _J = 25 °C		-	2.1	-		
Peak recovery current	IRRM	T _J = 125 °C		-	4	-	A	
Poverse recevery charge	Q _{rr}	T _J = 25 °C	VH - 100 V	-	19	-	nC	
Reverse recovery charge		Q _{rr}	T _J = 125 °C		-	60	-	nC

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C	
Thermal resistance, junction to mount	R _{thJM}	Device mounted on PCB with 2 x 3.5 mm soldering lands	-	7.7	14	°C/W	
Approximate weight				0.24		g	
Approximate weight				0.008		oz.	
Marking device		Case style SMC (DO-214AB)		31	-11		

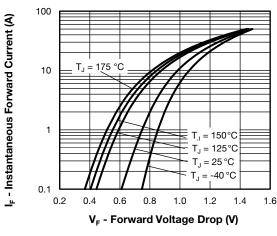


Fig. 1 - Typical Forward Voltage Drop Characteristics

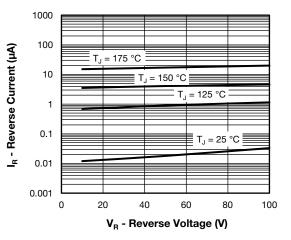
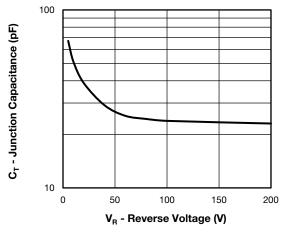


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

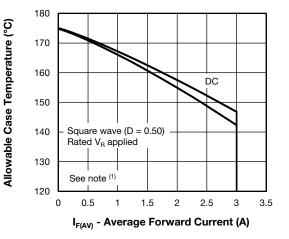


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

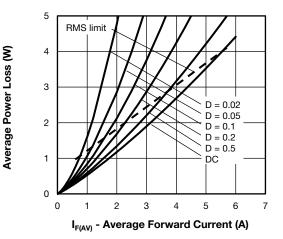


Fig. 5 - Forward Power Loss Characteristics

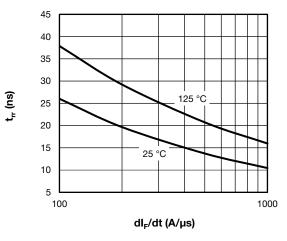
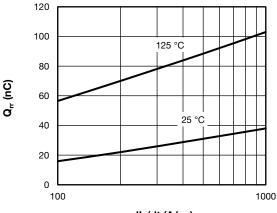


Fig. 6 - Typical Reverse Recovery Time vs. dI_F/dt



dl_F/dt (A/µs)

Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ 5); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

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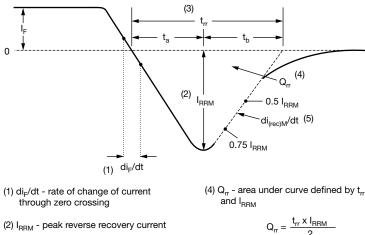
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VS-3ECH01HM3

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(3) $t_{\rm rr}$ - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

SHAY

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Device code	VS-	3	Е	с	Н	01	н	М3
	1	2	3	4	5	6	7	8
			-	niconduo le (3 = 3	•	oduct		
		- Circ	cuit conf	iguratior	-			
	4		single o SMC p					
	5		Process type, H = hyperfast recovery					
			Voltage code (01 = 100 V)					
				101 qua en-free,		comolia	nt and	termina
	0	- 1010	- naiog	en-nee,		compila	nt, and	termine

ORDERING INFORMATION (Example)								
PREFERRED P/N	PREFERRED P/N QUANTITY PER REEL MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION							
VS-3ECH01HM3/9AT	3500	3500	13"diameter plastic tape and reel					

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95402				
Part marking information	www.vishay.com/doc?95472				
Packaging information	www.vishay.com/doc?95404				

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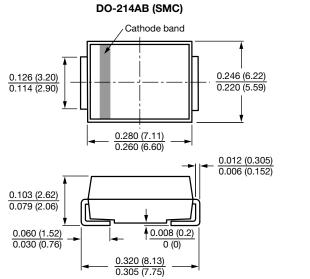


Outline Dimensions

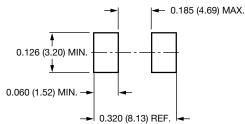
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DIMENSIONS in inches (millimeters)



Mounting Pad Layout





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